

ALTERNATIVE TO PTO/SB/08A/B
(Based on PTO 03-08 version)

Substitute for form 1449PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

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of

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		Complete if Known	
		Application Number	10/537,804
		Filing Date	June 7, 2005
First Named Inventor		Robert DWILINSKI	
Art Unit		1792	
Examiner Name		F.C. Hiteshew	
Attorney Docket Number		204552035400	

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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code* (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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				First Named Inventor	Robert DWILINSKI
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Examiner Signature	/Felisa Hiteshew/	Date Considered	10/07/2008
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